

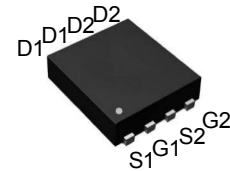
Features

- 60V/23A
 - $R_{DS(ON)}=20m\Omega(\text{typ.})@V_{GS}=10V$
 - $R_{DS(ON)}=25m\Omega(\text{typ.})@V_{GS}=4.5V$
- 100% UIS + R_g Tested
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)

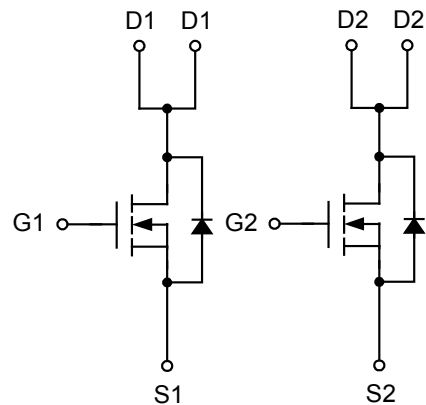
Applications

- Battery Protection.
- Load Switching.
- Bridge Topologies.

Pin Description



Top View of DFN3.3x3.3-8-EP



N-Channel MOSFET

Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ Unless Otherwise Noted)

Symbol	Parameter		Rating	Unit
Common Ratings				
V _{DSS}	Drain-Source Voltage		60	V
V _{GSS}	Gate-Source Voltage		±20	
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to 150	
I _S	Diode Continuous Forward Current	T _A =25°C	23	A
I _D	Continuous Drain Current	T _A =25°C	23	A
		T _A =70°C	14	
I _{DM} ^a	Pulsed Drain Current	T _A =25°C	69	
P _D	Maximum Power Dissipation	T _A =25°C	1.67	W
		T _A =70°C	1.07	
R _{θJC}	Thermal Resistance-Junction to Case	Steady state	7.8	°C/W
R _{θJA} ^b	Thermal Resistance-Junction to Ambient	Steady state	75	°C/W
I _{AS} ^c	Avalanche Current, Single pulse	L=0.5mH	11	A
E _{AS} ^c	Avalanche Energy, Single pulse	L=0.5mH	30.25	mJ

Note a : Pulse width limited by max. junction temperature.

Note b : Surface mounted on 1in^2 pad area.

Note c : UIS tested and pulse width limited by maximum junction temperature 150°C (initial temperature $T_J=25^{\circ}\text{C}$).

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

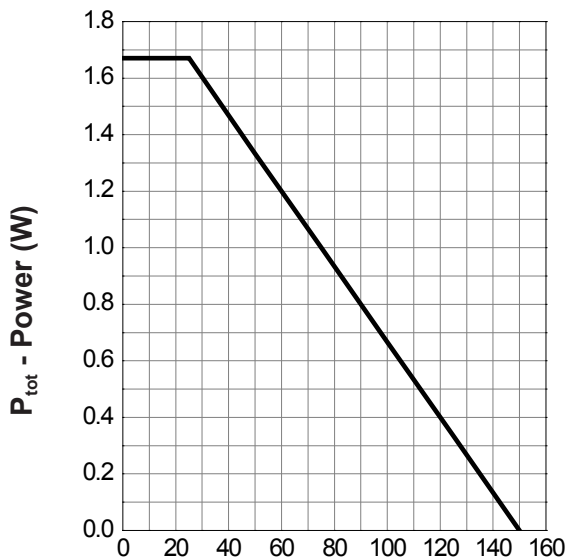
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	60	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =48V, V _{GS} =0V T _J =85°C	-	-	1 30	μA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	1	2	3	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)} ^d	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =4A V _{GS} =4.5V, I _{DS} =3A	-	20 25	28 32	mΩ
Diode Characteristics						
V _{SD} ^d	Diode Forward Voltage	I _{SD} =2A, V _{GS} =0V	-	0.8	1.3	V
t _{rr}	Reverse Recovery Time	I _{SD} =4A, dI _{SD} /dt=100A/μs	-	21.5	-	ns
Q _{rr}	Reverse Recovery Charge		-	18.1	-	nC
Dynamic Characteristics ^e						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz	-	1	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =30V, Frequency=1.0MHz	-	710	923	pF
C _{oss}	Output Capacitance		-	142	-	
C _{rss}	Reverse Transfer Capacitance		-	20	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =30V, R _L =30Ω, I _{DS} =1A, V _{GEN} =10V, R _G =6Ω	-	11	20	ns
t _r	Turn-on Rise Time		-	6	11	
t _{d(OFF)}	Turn-off Delay Time		-	22	40	
t _f	Turn-off Fall Time		-	15	27	
Gate Charge Characteristics ^e						
Q _g	Total Gate Charge	V _{DS} =30V, V _{GS} =4.5V, I _{DS} =4A	-	6	-	nC
Q _g	Total Gate Charge	V _{DS} =30V, V _{GS} =10V, I _{DS} =4A	-	12.1	17	
Q _{gs}	Gate-Source Charge		-	2.2	-	
Q _{gd}	Gate-Drain Charge		-	2.1	-	

Note d : Pulse test ; pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

Note e : Guaranteed by design, not subject to production testing.

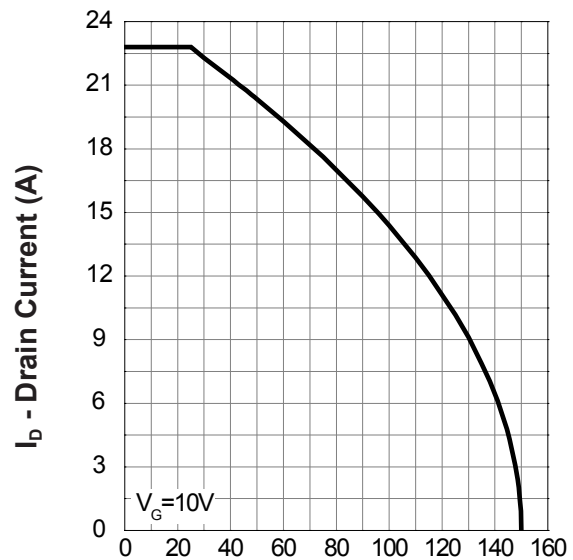
Typical Operating Characteristics

Power Dissipation



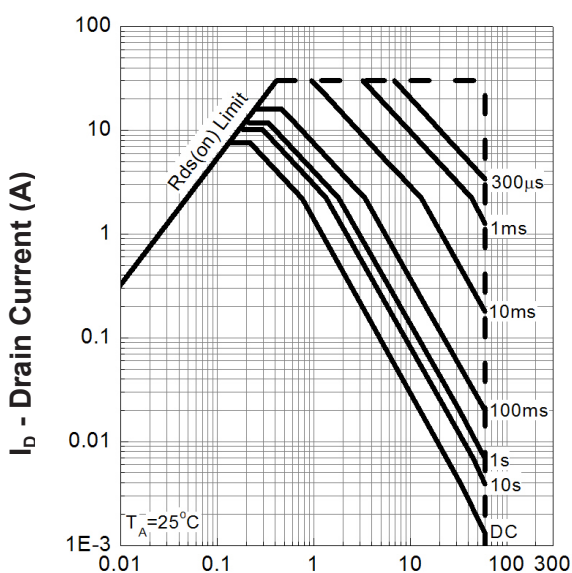
T_A - Ambient Temperature (°C)

Drain Current



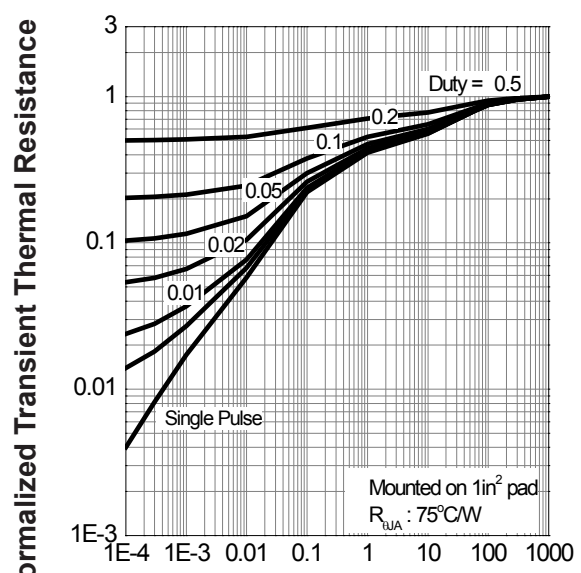
T_A - Ambient Temperature (°C)

Safe Operation Area



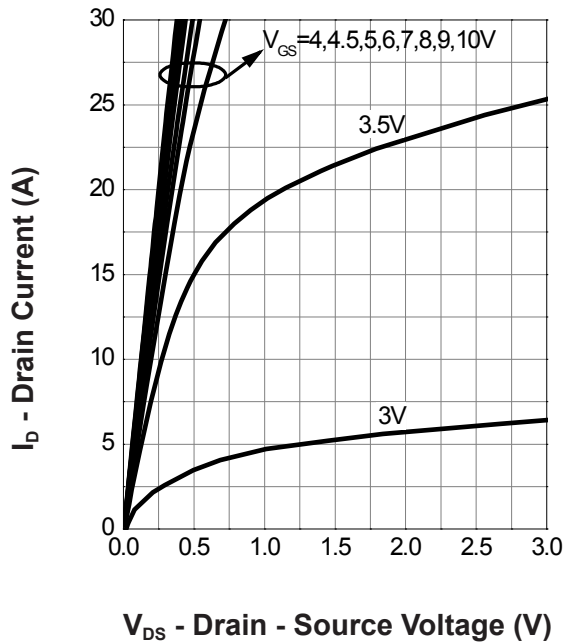
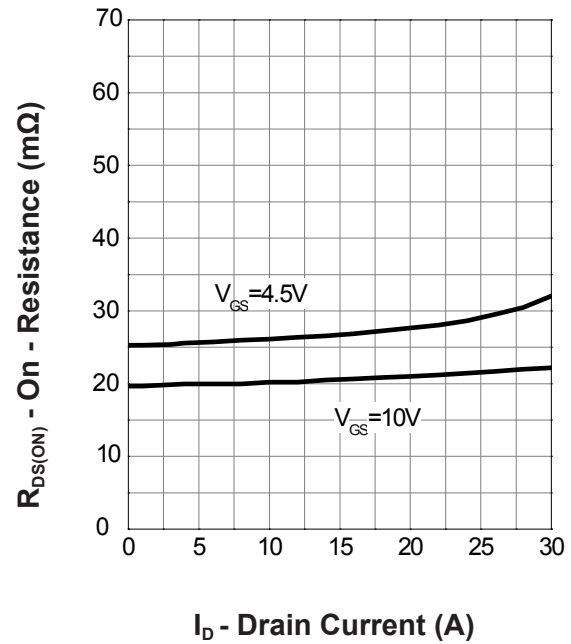
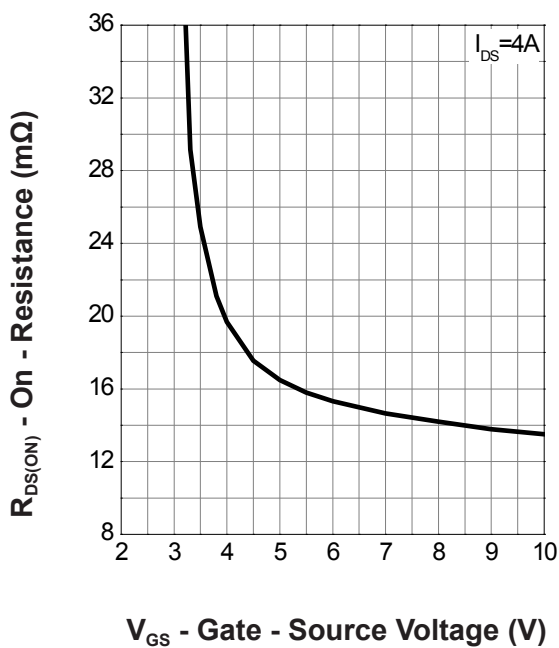
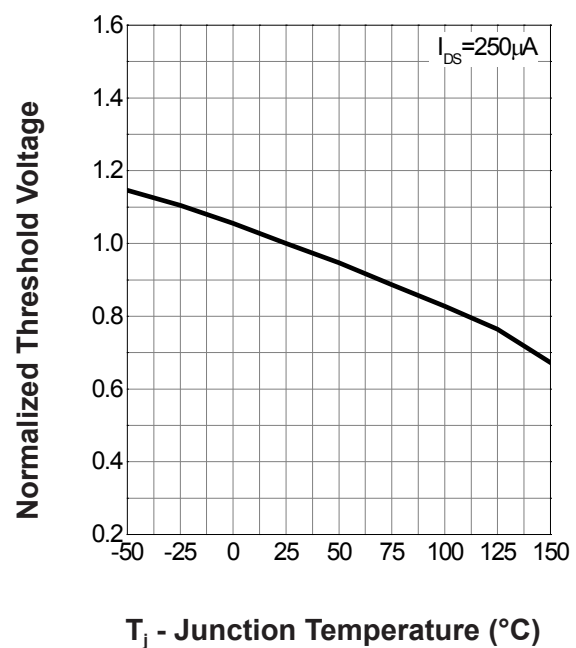
V_{DS} - Drain - Source Voltage (V)

Thermal Transient Impedance



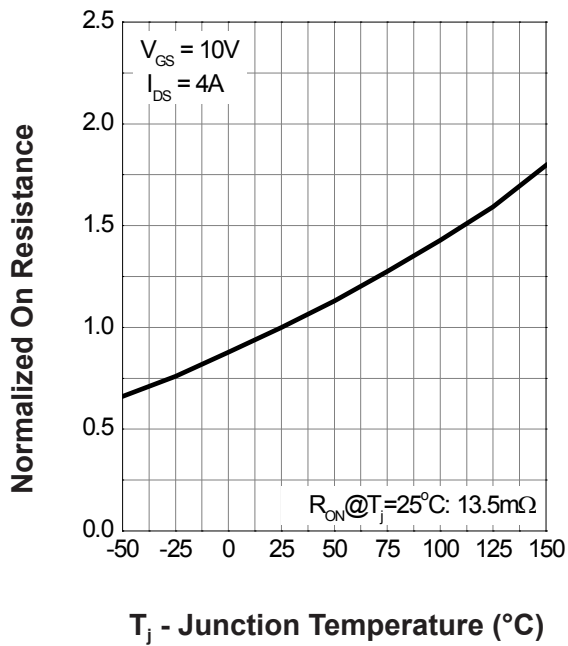
Square Wave Pulse Duration (sec)

Typical Operating Characteristics(Cont.)

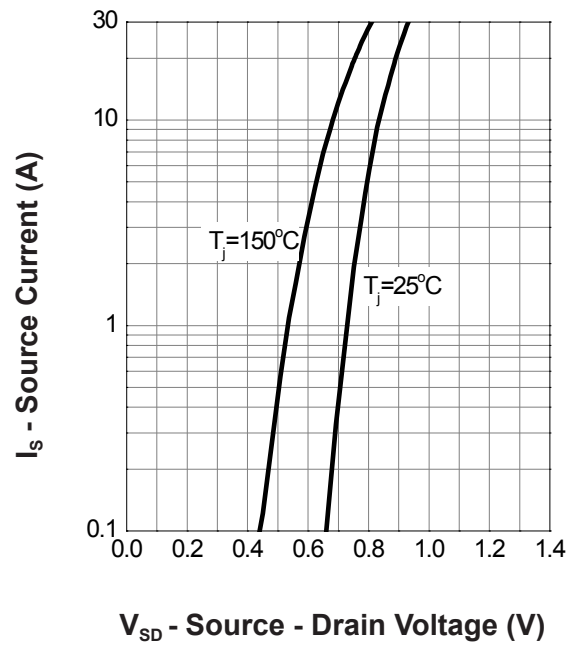
Output Characteristics

Drain-Source On Resistance

Gate-Source On Resistance

Gate Threshold Voltage


Typical Operating Characteristics(Cont.)

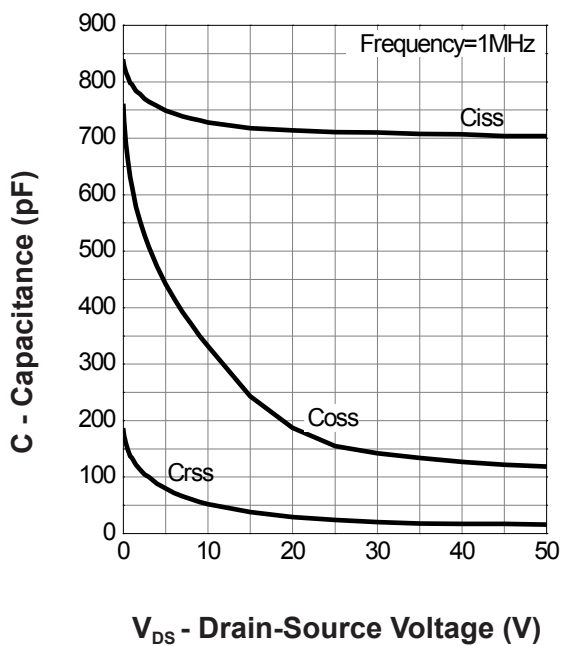
Drain-Source On Resistance



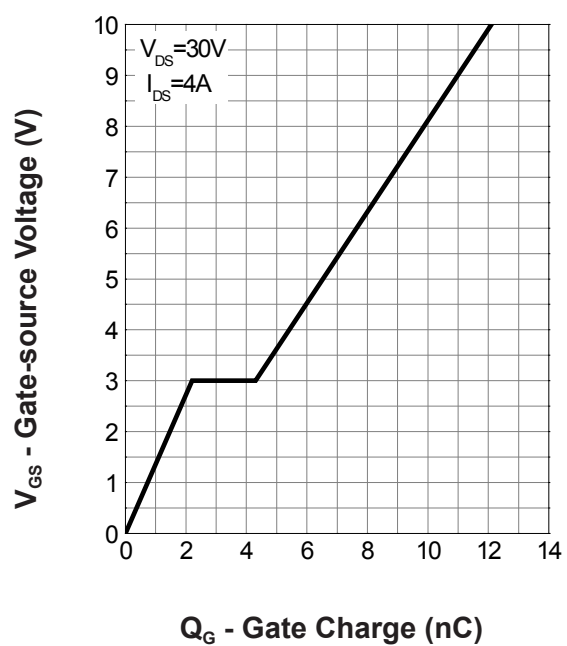
Source-Drain Diode Forward



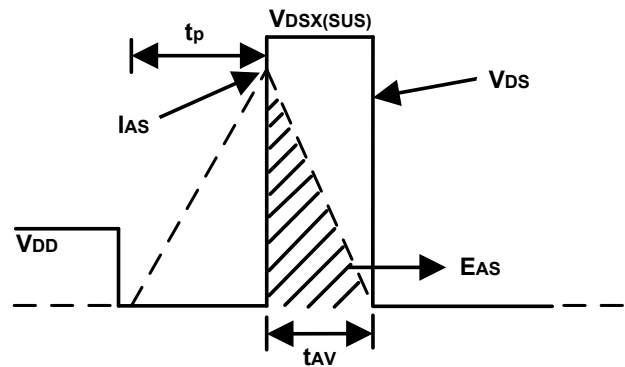
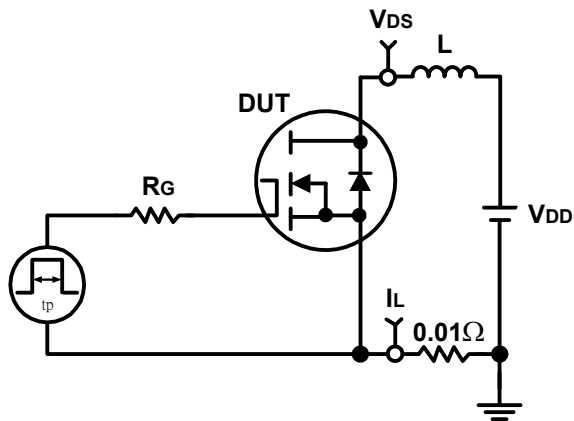
Capacitance



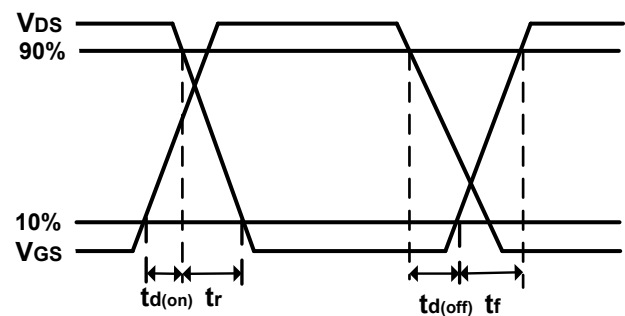
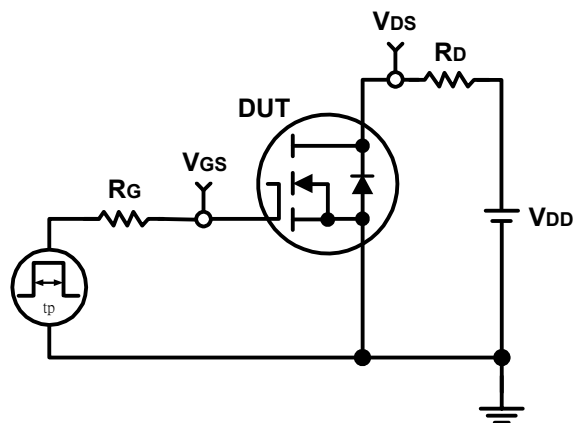
Gate Charge



Avalanche Test Circuit and Waveforms

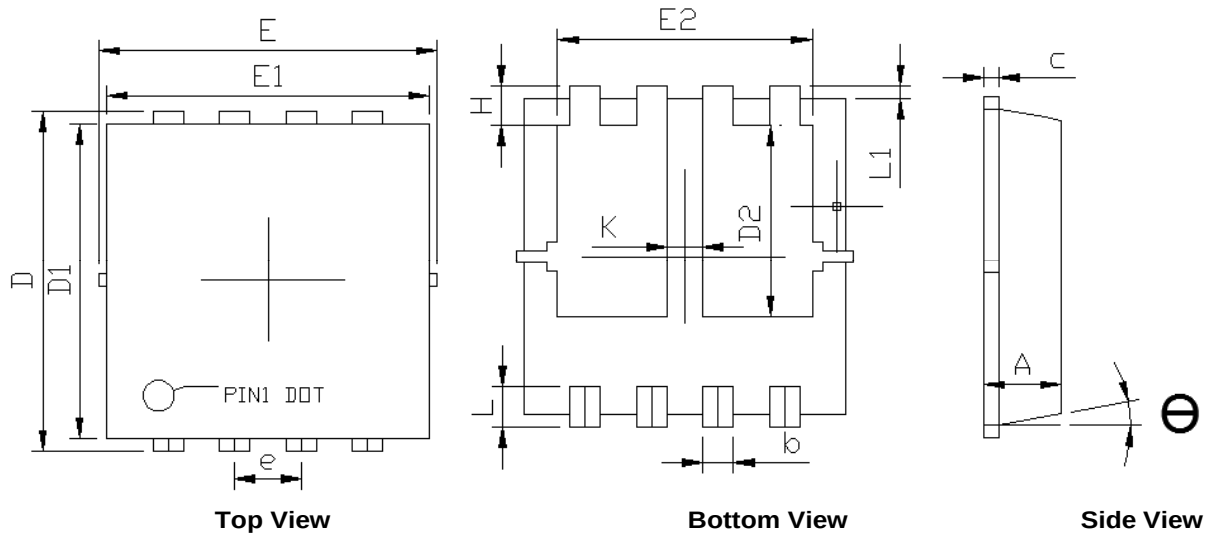


Switching Time Test Circuit and Waveforms



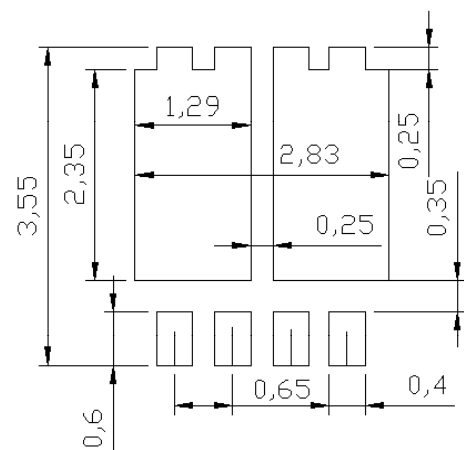
Package Information

DFN3.3x3.3-8L_EP2_P



SYMBOLS	DFN3.3x3.3G-8_EP2_P			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	0.70	0.80	0.028	0.031
b	0.25	0.35	0.010	0.014
c	0.10	0.25	0.004	0.010
D	3.25	3.45	0.128	0.136
D1	3.00	3.20	0.118	0.126
D2	1.78	1.98	0.070	0.078
E	3.20	3.40	0.126	0.134
E1	3.00	3.20	0.118	0.126
E2	2.39	2.59	0.094	0.102
e	0.65BSC		0.026 BSC	
H	0.30	0.50	0.012	0.020
L	0.30	0.50	0.012	0.020
L1	0.13 REF		0.005 REF	
K	0.30	-	0.012	-
θ	-	12°	-	12°

RECOMMENDED LAND PATTERN



UNIT: mm